Abstracts

2-18 GHz, High-Efficiency, Medium-Power GaAs FET Amplifiers

H.Q. Tserng, S.R. Nelson and H.M. Macksey. "2-18 GHz, High-Efficiency, Medium-Power GaAs FET Amplifiers." 1981 MTT-S International Microwave Symposium Digest 81.1 (1981 [MWSYM]): 31-33.

A GaAs FET amplifier using a 600 µm gate width device has achieved ~ 300 mW output with 20-25% power-added efficiency across 2 to 18 GHz. With a 1350 µm FET, 0.5 W output power was obtained from 7 to 16.5 GHz. Extending its large-signal performance to 2 GHz appears feasible.

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